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## U.S. PATENT DOCUMENTS

Examiner Initial		Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
	AA			,			
	AB						
	AC						·
	AD						

## FOREIGN PATENT DOCUMENTS

		Document No.	Date	Country	Translation (Yes or No)
00-	AE	9-326506	12/16/97	Japan	Yes-Abstract/Discussed in the specification
	AF				

## OTHER DOCUMENTS

_DF	AG	D. Leonard et al.; "Direct formation of quantum-sized dots from uniform coherent islands of InGaAs on GaAs surfaces"; Applied Physics Letters; Vol. 63; No. 23; December 6 1993; pp. 3203-3205./Discussed in the specification.
QE PF	АН	K. Mukai et al.; "Self-Formed In <sub>0.5</sub> Ga <sub>0.5</sub> As Quantum Dots on GaAs Substrates Emitting at 1.3µm"; Japanese Journal of Applied Physics' Vol. 33; Part 2, No. 12A; December 1 1994; pp. L1710-1712./Discussed in the specification.
Al J. Oshinowo et al.; "Highly uni metalorganic chemical vapor d		J. Oshinowo et al.; "Highly uniform InGaAs/GaAs quantum dots (~15 nm) by metalorganic chemical vapor deposition"; Applied Physics Letters; Vol. 65; No. 11; September 12 1994; pp. 1421-1423./Discussed in the specification.
Examiner	Ran	Date Considered 5/1/05